

Technical Data

DIODE



maximum ratings

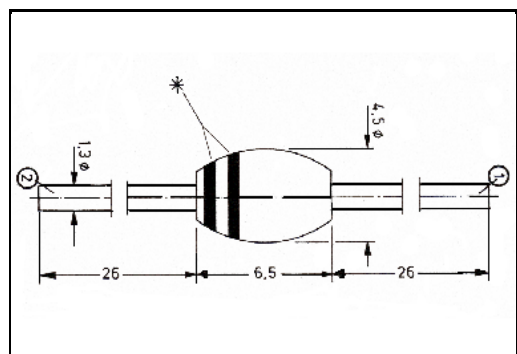
Voltage, Reverse (VR)	200.0	V	NO.	1N5550
Voltage, Reverse Peak (VRM)	200.0	V	TYPE	SILICON
Current at VR = 0V (IO)		A		RECTIFIER
Current Average Rectified (IF)	3.0	A		
Current Surge Peak (IFM)		A	CASE	SOD-64_1.3MM
Current, Surge (IFM) at tp = 8.3 ms	100.0	A		
Max. Power Dissipation (PT) at TC = °C		W		
Max. Thermal Resistance (Rth J-A)	70.0	°C/W		
Max. Junction Temperature (TJ)	175.0	°C		

PERFORMANCE CHARACTERISTICS at T_c = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS	MIN.	MAX.	UNITS
1.	VF	IF = 3.0 A (1)	-	1.0	V
2.	IR	VR = 200.0 V	-	1.0	μA
3.	IR	VR = 200.0 V, TA = 100.0° C	-	75.0	μA
4.	trr	IF = 0.5 A, IR = 1.0 A, ir = 0.25 A	-	2.0	μs
5.	CT	VR = 12.0 V, f = 1.0 MHz	-	100.0	pF
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Notes (1) pulse-tested tp ≤ 300 μs, duty cycle ≤ 2 %

DIMENSIONS in mm



Marking 1N5550
 Customer GENERAL PURPOSE